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BYV27 series

Ultra fast low-loss controlled avalanche rectifiers

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.

DESCRIPTION

Rugged glass SOD57 package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

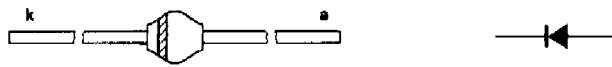
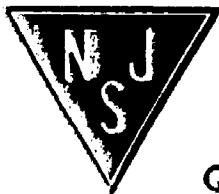


Fig.1 Simplified outline (SOD57) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		-	50	V
	BYV27-50				
	BYV27-100				
	BYV27-150				
	BYV27-200				
	BYV27-300				
	BYV27-400				
	BYV27-500				
V _R	continuous reverse voltage		-	50	V
	BYV27-50				
	BYV27-100				
	BYV27-150				
	BYV27-200				
	BYV27-300				
	BYV27-400				
	BYV27-500				
I _{F(AV)}	average forward current	T _{tp} = 85 °C; lead length = 10 mm; see Figs 2, 3 and 4; averaged over any 20 ms period; see also Figs 14, 15 and 16	-	2.0	A
	BYV27-50 to 200				
	BYV27-300 and 400				
	BYV27-500 and 600				
I _{F(AV)}	average forward current	T _{amb} = 60 °C; printed-circuit board mounting (see Fig. 25); see Figs 5, 6 and 7; averaged over any 20 ms period; see also Figs 14, 15 and 16	-	1.30	A
	BYV27-50 to 200				
	BYV27-300 and 400				
	BYV27-500 and 600				



Quality Semiconductors

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{FRM}	repetitive peak forward current BYV27-50 to 400 BYV27-500 and 600	$T_{tp} = 85^\circ\text{C}$; see Figs 8, 9 and 10	—	20 16	A A
I_{FRM}	repetitive peak forward current BYV27-50 to 200 BYV27-300 and 400 BYV27-500 and 600	$T_{amb} = 60^\circ\text{C}$; see Figs 11, 12 and 13	— — —	14 13 11	A A A
I_{FSM}	non-repetitive peak forward current BYV27-50 to 400 BYV27-500 and 600	$t = 10 \text{ ms half sine wave}$; $T_j = T_{j \max}$ prior to surge; $V_R = V_{RRM\max}$	— —	50 40	A A
E_{RSM}	non-repetitive peak reverse avalanche energy	$L = 120 \text{ mH}$; $T_j = T_{j \max}$ prior to surge; inductive load switched off	—	20	mJ
T_{stg}	storage temperature		-65	+175	°C
T_j	junction temperature	see Fig. 17	-65	+175	°C

ELECTRICAL CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage BYV27-50 to 200 BYV27-300 and 400 BYV27-500 and 600	$I_F = 2 \text{ A}$; $T_j = T_{j \max}$; see Figs 18, 19 and 20	— — —	— — —	0.78 0.82 1.00	V V V
V_F	forward voltage BYV27-50 to 200 BYV27-300 and 400 BYV27-500 and 600	$I_F = 2 \text{ A}$; see Figs 18, 19 and 20	— — —	— — —	0.98 1.05 1.25	V V V
$V_{(BR)R}$	reverse avalanche breakdown voltage BYV27-50 BYV27-100 BYV27-150 BYV27-200 BYV27-300 BYV27-400 BYV27-500 BYV27-600	$I_R = 0.1 \text{ mA}$	55 110 165 220 330 440 560 675	— — — — — — — —	— — — — — — — —	V V V V V V V V
I_R	reverse current	$V_R = V_{RRM\max}$; see Fig. 21	—	—	5	μA
		$V_R = V_{RRM\max}$; $T_j = 165^\circ\text{C}$; see Fig. 21	—	—	150	μA

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t_{rr}	reverse recovery time BYV27-50 to 200 BYV27-300 to 600	when switched from $I_F = 0.5 \text{ A}$ to $I_R = 1 \text{ A}$; measured at $I_R = 0.25 \text{ A}$; see Fig. 27	—	—	25	ns
C_d	diode capacitance BYV27-50 to 200 BYV27-300 and 400 BYV27-500 and 600	$f = 1 \text{ MHz}$; $V_R = 0$; see Figs 22, 23 and 24	—	100	—	pF
$\left \frac{dI_R}{dt} \right $	maximum slope of reverse recovery current	when switched from $I_F = 1 \text{ A}$ to $V_R \geq 30 \text{ V}$ and $dI_F/dt = -1 \text{ A}/\mu\text{s}$; see Fig. 26	—	—	4	A/ μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th j-tp}$	thermal resistance from junction to tie-point	lead length = 10 mm	46	K/W
$R_{th j-a}$	thermal resistance from junction to ambient	note 1	100	K/W